



BCV47Q

Description

This Bipolar Junction Transistor (BJT) is designed to meet the stringent requirements of automotive applications.

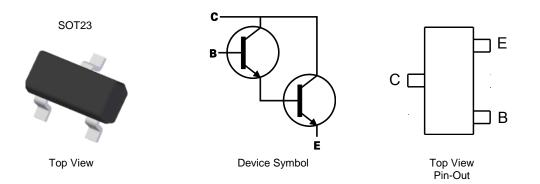
Features

- BV_{CEO} > 60V
- Darlington Transistor h_{FE} > 10k @ 100mA for High Gain
- $I_{C} = 500$ mA High Continuous Collector Current
- Complementary Darlington PNP Type: BCV46
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

60V NPN DARLINGTON TRANSISTOR IN SOT23

Mechanical Data

- Case: SOT23
- Case Material: Molded Plastic, "Green" molding compound
- UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 (3)
- Weight 0.008 grams (Approximate)



Ordering Information (Notes 4 & 5)

Part Number	Compliance	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
BCV47QTA	Automotive	ZFG	7	8	3,000
BCV47QTC	Automotive	ZFG	13	8	10,000

Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.

See http://www.diodes.com for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + CI) and

<1000ppm antimony compounds.

4. Automotive products are AEC-Q101 qualified and are PPAP capable. Refer to http://www.diodes.com/quality/product_compliance_definitions/.

5. For packaging details, go to our website at http://www.diodes.com.

Marking Information

		=											
				SOT23									
				Π		ZFG = Product Type Marking Code							
				ZFG >		YM = Date Code Marking Y or \overline{Y} = Year (ex: E = 2017) M or \overline{M} = Month (ex: 9 = September)							
Date Code Key													
Year	2017	2018	2019	2020	2021	2022	2023	2024	2025	2026	2027	2028	
Code	E	F	G	Н	I	J	K	L	М	Ν	0	Р	
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec	
Code	1	2	3	4	5	6	7	8	9	0	Ν	D	



Absolute Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	80	V
Collector-Emitter Voltage	V _{CEO}	60	V
Emitter-Base Voltage	V _{EBO}	10	V
Continuous Collector Current	lc	500	mA
Peak Pulse Current	Ісм	800	mA
Base Current	Ι _Β	100	mA

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Power Dissipation	(Note 6)	D	310	mW
	(Note 7)	PD	350	11177
Thermal Resistance, Junction to Ambient	(Note 6)	D	403	°C/W
	(Note 7)	R _{0JA}	357	C/VV
Thermal Resistance, Junction to Leads (Note 8)		R _{θJL}	350	°C/W
Operating and Storage Temperature Range		TJ,TSTG	-55 to +150	°C

ESD Ratings (Note 9)

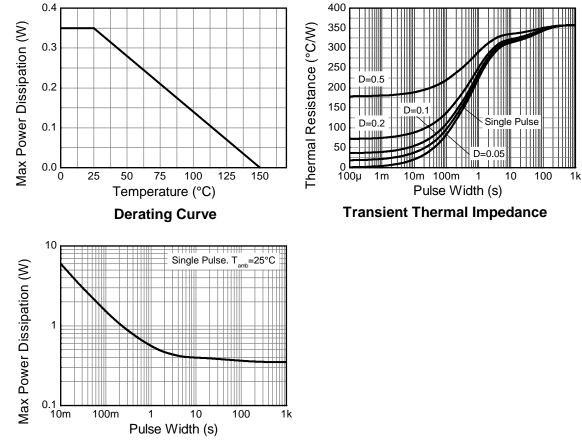
Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	2,000	V	2
Electrostatic Discharge - Machine Model	ESD MM	200	V	В

6. For the device mounted on minimum recommended pad layout FR4 PCB with high coverage of single sided 1oz copper in still air condition; the device is Notes: not the device incurred on minimum teconimended pad tayout FR4 PCB with measured when operating in a steady-state condition.
Same as note (6), except the device is mounted on 15mm x 15mm FR4 PCB.
Thermal resistance from junction to solder-point (at the end of the leads).
Refer to JEDEC specification JESD22-A114 and JESD22-A115.



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Thermal Characteristics and Derating Information (@T_A = +25°C, unless otherwise specified.)



Pulse Power Dissipation



Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

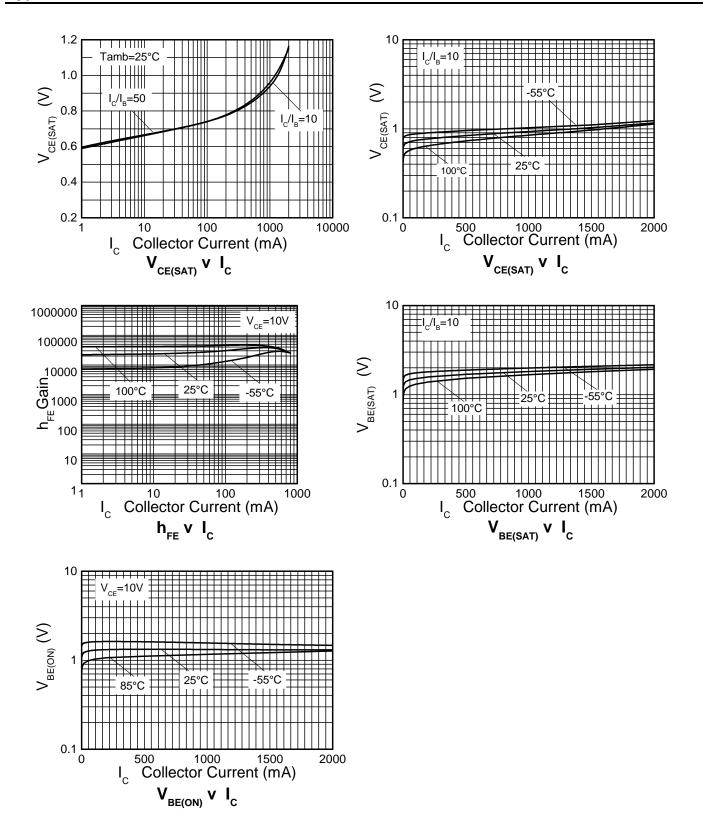
	• • •		-			
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS						
Collector-Base Breakdown Voltage	BV _{CBO}	80			V	$I_{\rm C} = 100 \mu {\rm A}$
Collector-Emitter Breakdown Voltage (Note 10)	BVCEO	60	_		V	$I_{CEO} = 10 \text{mA}$
Emitter-Base Breakdown Voltage	BV _{EBO}	10	_	_	V	$I_{EBO} = 10 \mu A$
Collector cut-off current	1	_	<1	100	nA	$V_{CB} = 60V$
	I _{CBO}	—		10	μA	V _{CB} = 60V, T _A = +150°C
Emitter-base Cut-off Current	I _{EBO}	_	<1	100	nA	$V_{EB} = 4V$
ON CHARACTERISTICS (Note 10)						
Static Forward Current Transfer Ratio	hFE	2,000 4,000 10,000 2,000	_	_	_	$\begin{split} I_{C} &= 100 \mu A, \ V_{CE} = 1 V \\ I_{C} &= 10 m A, \ V_{CE} = 5 V \\ I_{C} &= 100 m A, \ V_{CE} = 5 V \\ I_{C} &= 500 m A, \ V_{CE} = 5 V \end{split}$
Collector-Emitter Saturation Voltage	V _{CE(sat)}	_	_	1.0	V	$I_{\rm C} = 100 {\rm mA}, I_{\rm B} = 0.1 {\rm mA}$
Base-Emitter Saturation Voltage	V _{BE(sat)}	_	_	1.5	V	$I_{\rm C} = 100 {\rm mA}, I_{\rm B} = 0.1 {\rm mA}$
SMALL SIGNAL CHARACTERISTICS (Note 10)						
Transition Frequency	f _T	_	170	_	MHz	$I_C = 50$ mA, $V_{CE} = 5$ V, f = 20MHz
Output Capacitance	C _{obo}	—	3.5		pF	V _{CB} = 10V, f = 1MHz

Note: 10. Measured under pulsed conditions. Pulse width \leq 300µs. Duty cycle \leq 2%.



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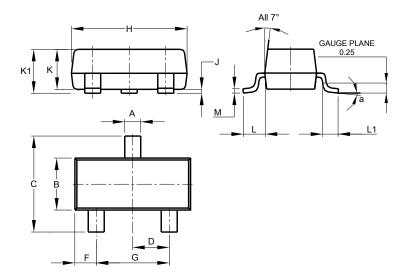
Typical Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)





Package Outline Dimensions

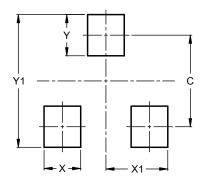
Please see http://www.diodes.com/package-outlines.html for the latest version.



SOT23							
Dim	Min	Max	Тур				
Α	0.37	0.51	0.40				
В	1.20	1.40	1.30				
С	2.30	2.50	2.40				
D	0.89	1.03	0.915				
F	0.45	0.60	0.535				
G	1.78	2.05	1.83				
Н	2.80	3.00	2.90				
J	0.013	0.10	0.05				
K	0.890	1.00	0.975				
K1	0.903	1.10	1.025				
L	0.45	0.61	0.55				
L1	0.25	0.55	0.40				
Μ	0.085	0.150	0.110				
а	0°	8°					
All	All Dimensions in mm						

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.



Dimensions	Value (in mm)
С	2.0
Х	0.8
X1	1.35
Y	0.9
Y1	2.9



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